

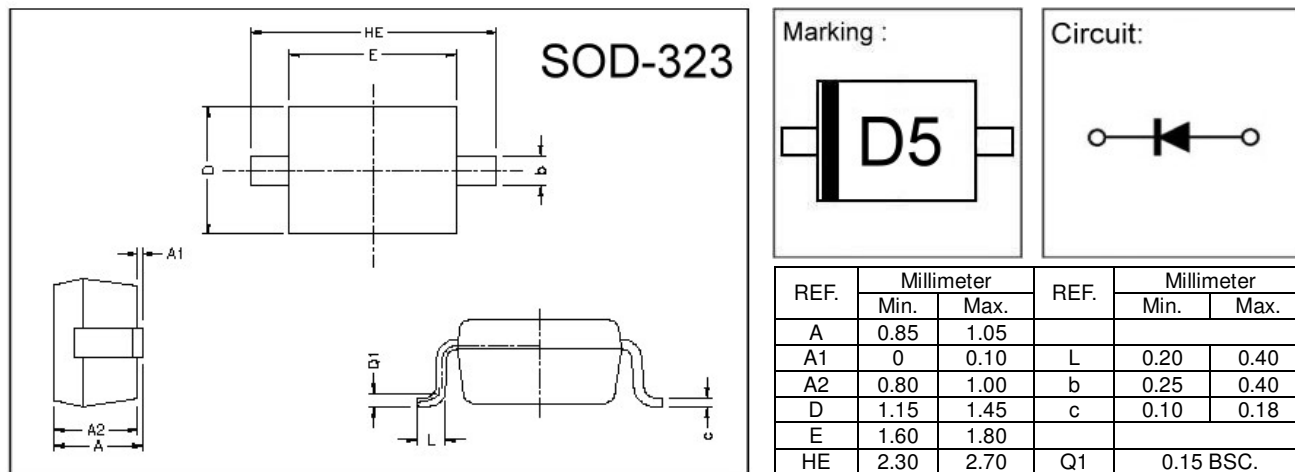
GD511 SURFACE MOUNT, SWITCHING DIODE

VOLTAGE 85V, CURRENT 0.1A

Description

The GD511 is designed for ultra high speed switching application, low forward voltage and fast reverse recovery time.

Package Dimensions



Absolute Maximum Ratings at Ta = 25°C

Parameter	Symbol	Ratings	Unit
Junction Temperature	T _j	+150	°C
Storage Temperature	T _{stg}	-55 ~ +150	°C
Maximum Peak Reverse Voltage	V _{RM}	85	V
Maximum Reverse Voltage	V _R	80	V
Maximum (Peak) Forward Current	I _{FM}	300	mA
Average Forward Current	I _O	100	mA
Surge Current(10ms)	I _{FSM}	2	A
Total Power Dissipation	P _D	150	mW

Electrical Characteristics at Ta = 25°C

Characteristic	Symbol	Min.	Typ.	Max.	Unit	Test Conditions
Forward Voltage	V _F (1)	-	0.6	-	V	I _F =1mA
	V _F (2)	-	0.7	-	V	I _F =10mA
	V _F (3)	-	0.9	1.2	V	I _F =100mA
Reverse Current	I _R	-	-	0.5	μA	V _R =80V
Total Capacitance	C _T	-	2.2	4.0	pF	V _R =0, f=1MHz
Reverse Recovery Time	T _{rr}	-	1.6	4.0	nS	I _F =10mA

Characteristics Curve

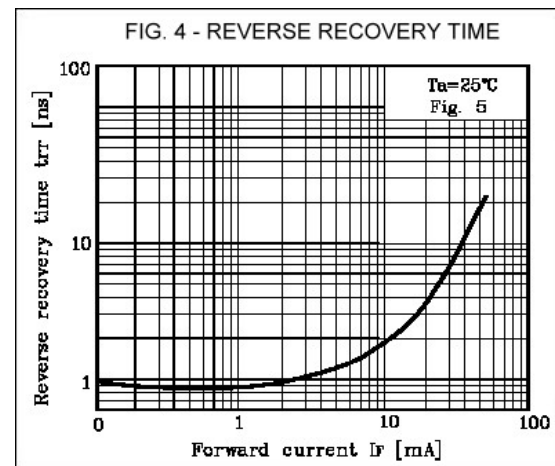
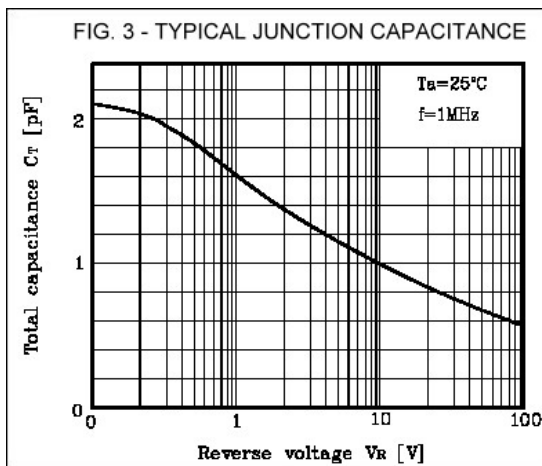
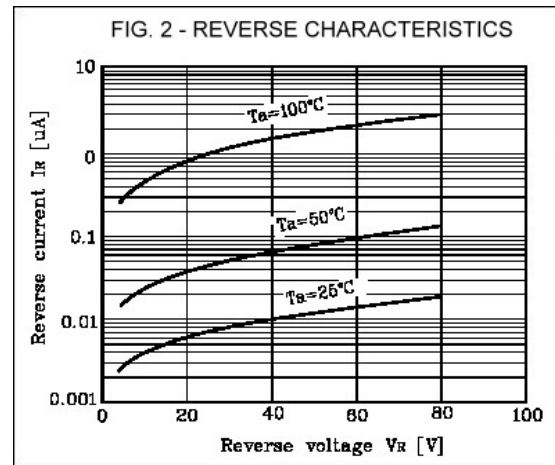
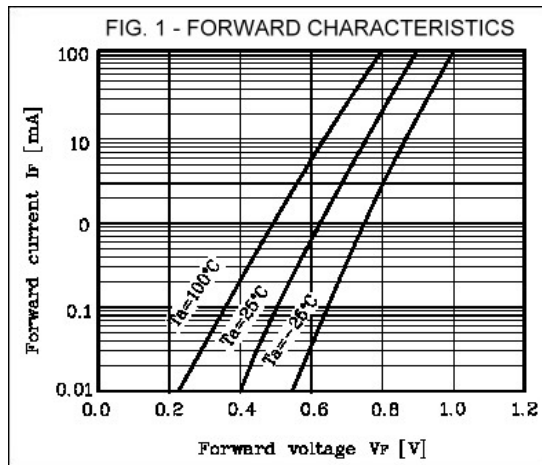
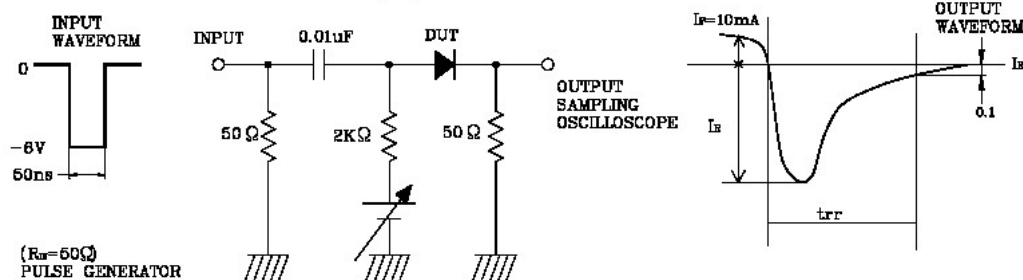


FIG. 5 - REVERSE RECOVERY TIME(t_{rr}) TEST CIRCUIT



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